L Number	Hits	Search Text	DB	Time stamp
1	1	6159643.pn.	USPAT	2004/08/12 11:03
2	45	Goldstein-Michael.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/12
_	15760	((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)	USPAT	2004/07/27 12:18
-	1823	(((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)	USPAT	2004/06/28 10:48
_	97	((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj	USPAT	2004/06/28 12:12
_	285	expansion) or (titanium adj silicate)) ((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3	USPAT	2004/06/28 12:13
<u>-</u> -	272	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or	USPAT	2004/06/28 12:13
	·	<pre>cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3) not (((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))</pre>		
_	243	<pre>((((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3) not ((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))) and @ay<=2001</pre>	USPAT	2004/06/28 12:46
	226	((((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3) not ((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))) and @ay<=2001) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2004/06/28 12:47

-	28163	((crystall\$3 near3 silicon) or	USPAT	2004/07/27
		(poly\$1crystalline adj silicon) or		12:18
		polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)		
-	1499	(((crystall\$3 near3 silicon) or	USPAT	2004/07/27
		(poly\$1crystalline adj silicon) or		12:24
		polysilicon or TiSi or (titanium adj		
		silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2))		
_	264	(((crystall\$3 near3 silicon) or	USPAT	2004/07/27
		(poly\$1crystalline adj silicon) or	OSFAI	13:46
		polysilicon or TiSi or (titanium adj		100
		silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)) and (sacrificial with		
		(oxide or dioxide or SiO or SiO?sub.2)		
1_	264	same (isotropic\$3 or (wet adj etch\$3)))	Hann	2004/07/27
	204	(((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or	USPAT	2004/07/27
		polysilicon or TiSi or (titanium adj		12:20
		silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
1		planarization)) and (((sacrificial with		
		(oxide or dioxide or SiO or SiO?sub.2))		
	000	same (isotropic\$3 or (wet adj etch\$3))))	1	
-	232		USPAT	2004/07/27
-		(poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj		12:26
		silicate) or ceramic) and (polish or		
1		polishing or cmp or planarize or		
		planarization)) and (((sacrificial with		
		(oxide or dioxide or SiO or SiO?sub.2))		
		<pre>same (isotropic\$3 or (wet adj etch\$3)))))</pre>		1
	1	and @ay<=2001		
_	185	(((((crystall\$3 near3 silicon) or	USPAT	2004/07/27
		(poly\$1crystalline adj silicon) or		12:27
		polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)) and (((sacrificial with		
		(oxide or dioxide or SiO or SiO?sub.2))		
		<pre>same (isotropic\$3 or (wet adj etch\$3)))))</pre>		
		and @ay<=2001) and (photo\$11ithograph\$3		
_	100	or lithograph\$3)		00044
	169	(((((crystall\$3 near3 silicon) or	USPAT	2004/07/27
		<pre>(poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj</pre>		13:24
		silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)) and (((sacrificial with		
	.	(oxide or dioxide or SiO or SiO?sub.2))		
		<pre>same (isotropic\$3 or (wet adj etch\$3)))))</pre>		
		and @ay<=2001) and (photo\$11ithograph\$3		
_	7	or lithograph\$3)) and semiconductor		0004/07/55
	'	("5171699" "5194394" "5340756" "5387528" "5404040" "5656520"	USPAT	2004/07/27
		"5668026").PN.		13:21
_	4259	(CTE or (coefficient adj3 thermal adj	USPAT	2004/07/27
	.200	expansion)) and (polish or polished or	JULAI	13:46
		polishing or cmp or planarize or		-3.10
		planarizing)		

-	4253		USPAT	2004/07/27
		expansion)) and (polish or polished or		13:46
		polishing or cmp or planarize or		
	1	planarizing)) not ((((((crystall\$3 near3		
		silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or		1
		(titanium adj silicate) or ceramic) and		
		(polish or polishing or cmp or planarize		
		or planarization)) and (((sacrificial		
		with (oxide or dioxide or SiO or		
Ì		SiO?sub.2)) same (isotropic\$3 or (wet adj		
		etch\$3))))) and @ay<=2001) and		
		<pre>(photo\$1lithograph\$3 or lithograph\$3))</pre>		
		and semiconductor)		
-	1499		USPAT	2004/07/27
		(poly\$1crystalline adj silicon) or		13:48
		polysilicon or TiSi or (titanium adj		
		silicate) or ceramic) and (polish or		
		polishing or cmp or planarize or		
		planarization)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2))		
_	77		110000	2004/07/05
	''	expansion)) and (polish or polished or	USPAT	2004/07/27
		polishing or cmp or planarize or		14:28
		planarizing)) not (((((crystall\$3 near3		
		silicon) or (poly\$1crystalline adj		
		silicon) or polysilicon or TiSi or		
	1	(titanium adj silicate) or ceramic) and		
		(polish or polishing or cmp or planarize	1	
		or planarization)) and (((sacrificial		
1		with (oxide or dioxide or SiO or		
		SiO?sub.2)) same (isotropic\$3 or (wet adj		
		etch\$3))))) and @ay<=2001) and		
		(photo\$11ithograph\$3 or lithograph\$3))		
		and semiconductor)) and (sacrificial with		
_	26	(oxide or dioxide or SiO or SiO?sub.2))		0004/05/05
	20	(mirror with photo\$1lithograph\$3).clm.	USPAT	2004/07/27
_	425	mirror with photo\$11ithograph\$3	USPAT	15:30 2004/07/27
		marror wrom photography 5	USPAI	15:30
_	3060	(mirror or glass) with	USPAT	2004/07/27
		photo\$11ithograph\$3	001111	15:30
-	507	((mirror or glass) with	USPAT	2004/07/27
		photo\$11ithograph\$3) and (polish or		15:31
		polishing or cmp or planarization or		
		planarize or planarizing)		
-	326	(((mirror or glass) with	USPAT	2004/07/27
		photo\$1lithograph\$3) and (polish or		15:32
		polishing or cmp or planarization or		
		planarize or planarizing)) and (sacrificial or (silicon adj oxide) or		
	1	(silicon adj dioxide) or SiO or		
]	SiO?sub.2)		
~	307	((((mirror or glass) with	USPAT	2004/07/27
		photo\$1lithograph\$3) and (polish or	ODIAI	15:33
		polishing or cmp or planarization or		13.33
		planarize or planarizing)) and		
		(sacrificial or (silicon adj oxide) or		
		(silicon adj dioxide) or SiO or		
		SiO?sub.2)) and @ay<=2001		
_	213	(((((mirror or glass) with	USPAT	2004/07/27
		photo\$1lithograph\$3) and (polish or		15:37
		polishing or cmp or planarization or		
		planarize or planarizing)) and (sacrificial or (silicon adj oxide) or		
		(silicon adj dioxide) or SiO or		
		SiO?sub.2)) and @ay<=2001) and (crystal		
		or crytalline or poly\$1silicon or		
		poly\$1crystalline)		

-	174	<pre>((((((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)) and (sacrificial or (silicon adj oxide) or (silicon adj dioxide) or SiO or</pre>	USPAT	2004/07/27 15:37
		<pre>si0?sub.2)) and @ay<=2001) and (crystal or crytalline or poly\$1silicon or poly\$1crystalline)) and semiconductor</pre>		
_	5187	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)	USPAT	2004/08/10 16:46
-	4348	(((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor	USPAT	2004/08/10 10:43
_	1443	<pre>((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)</pre>	USPAT	2004/08/10 15:54
	314	<pre>(((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and (((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))</pre>	USPAT	2004/08/10
-	289	(((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and (((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))) and @ay<=2001	USPAT	2004/08/10 10:45
-	270	((((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and (((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))) and @ay<=2001) and (etch or etching)	USPAT	2004/08/10 10:48
	203	<pre>((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing or polished or planarize\$1 or planarizing or cmp) with (crystalline or poly\$1silicon))</pre>	USPAT	2004/08/10 15:55
-	157	(((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing or polished or planarize\$1 or planarizing or cmp) with (crystalline or poly\$1silicon))) not (((((((titanium adj silicate) or TiSiO or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and (((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))) and @ay<=2001) and (etch or etching))	USPAT	2004/08/10 15:55

-	141	((((((titanium adj silicate) or TiSi or	USPAT	2004/08/10
		Tisio or ceramic) and (crystalline adj		15:55
		(Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing		
	İ	or polished or planarize\$1 or planarizing		
	ľ	or cmp) with (crystalline or		
		poly\$1silicon))) not ((((((titanium adj		
		silicate) or TiSi or TiSiO or ceramic)		
		and (crystalline adj (Si or silicon) or		
		poly\$1silicon)) and semiconductor) and		
		(polish or polishing or polished or planarize\$1 or planarizing or cmp)) and		
		(((silicon adj dioxide) or (silicon adj		
		oxide) or SiO or SiO?sub.2) with (thermal		
		or grow or growing))) and @ay<=2001) and		
		(etch or etching))) and @ay<=2001		
_	623	titanium adj silicate	USPAT	2004/08/10
	12	/#####################################		16:46
-	43	(titanium adj silicate) and (polish or polishing or cmp or planarize or	USPAT	2004/08/10
		polishing or cmp or planarize or planarizing)		17:34
_	5	("5272744" "5978441" "6048652"	USPAT	2004/08/10
		"6159643" "6159824").PN.	JULIA	16:49
-	44		USPAT	2004/08/10
		planarize or planarizing)		17:34
-	17		USPAT	2004/08/10
* .		planarize or planarizing)) and (crystal		17:34
_	7	or crystalline or poly\$1silicon) ("2326059" "5154744" "5506080"	TIGD DE	0004/00/5-
	/	(2326039	USPAT	2004/08/10
	İ	"6178221").PN.		17:39
_	5879	(ULE or (thermal adj expansion) or CTE!	USPAT	2004/08/11
		or zerodur) and (polish or polishing or	001111	12:03
		cmp or planarize or planarizing)		
-	1315	((ULE or (thermal adj expansion) or CTE!	USPAT	2004/08/11
		or zerodur) and (polish or polishing or		12:04
		<pre>cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon)</pre>		
		or si)) or polysilicon)		
_	1227	(((ULE or (thermal adj expansion) or CTE!	USPAT	2004/08/11
		or zerodur) and (polish or polishing or	ODITI	10:44
		cmp or planarize or planarizing)) and		
		(((crystalline or crystal) near3 (silicon		
1_	C4.5	or si)) or polysilicon)) and @ay<=2001		
_	646	((((ULE or (thermal adj expansion) or	USPAT	2004/08/11
i		CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and		10:44
]	(((crystalline or crystal) near3 (silicon		
		or si)) or polysilicon)) and @ay<=2001)		
		and (lithography or lithographic or		
		photo\$11ithograph\$2)		
-	501	(((((ULE or (thermal adj expansion) or	USPAT	2004/08/11
		CTE! or zerodur) and (polish or polishing		12:03
		or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon		
		or si)) or polysilicon) and @ay<=2001)		·
		and (lithography or lithographic or		
		photo\$1lithograph\$2)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or si0 or		
	المال	SiO?sub.2)		
-	187	(((((ULE or (thermal adj expansion) or	USPAT	2004/08/11
		CTE! or zerodur) and (polish or polishing		11:34
		or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon		
		or si)) or polysilicon)) and @ay<=2001)		
.		and (lithography or lithographic or		
		photo\$11ithograph\$2)) and (((silicon adj		
		oxide) or (silicon adj dioxide) or siO or		
		SiO?sub.2) with (thermal or anneal or		
L		annealling))		

_	19	(USPAT	2004/08/11
		"5122852" "5201996" "5286335"		11:11
		"5344517" "5391257" "5641381"		
		"5764820" "5985742" "6010579"		
		"6120597" "6159323" "6159824" "6159825" "6162705" "6204151"		
		"6159825" "6162705" "6204151" "6303468").PN.		
_	7		USPAT	2004/08/11
	1	"5510230" "6048652" "6159643"	USPAI	11:12
		"6178221").PN.		11.12
-	314	((((((ULE or (thermal adj expansion) or	USPAT	2004/08/11
		CTE! or zerodur) and (polish or polishing		11:34
		or cmp or planarize or planarizing)) and		
		(((crystalline or crystal) near3 (silicon		
		or si)) or polysilicon)) and @ay<=2001)	,	
		and (lithography or lithographic or		
		photo\$11ithograph\$2)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or siO or		
		SiO?sub.2)) not ((((((ULE or (thermal adjexpansion) or CTE! or zerodur) and		
		(polish or polishing or cmp or planarize		
		or planarizing)) and (((crystalline or		
		crystal) near3 (silicon or si)) or		
		polysilicon)) and @ay<=2001) and		
		(lithography or lithographic or		
		photo\$1lithograph\$2)) and (((silicon adj		
		oxide) or (silicon adj dioxide) or siO or		
		Si0?sub.2) with (thermal or anneal or annealling)))		
_	114	<pre> annealling;;; ((((((ULE or (thermal.adj expansion) or</pre>	11CD 3 M	2004/00/11
	114	CTE! or zerodur) and (polish or polishing	USPAT	2004/08/11
		or cmp or planarize or planarizing)) and		11.54
		(((crystalline or crystal) near3 (silicon		
		or si)) or polysilicon)) and @ay<=2001)		1
		and (lithography or lithographic or		
		photo\$1lithograph\$2)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or siO or		1
		SiO?sub.2)) not ((((((ULE or (thermal adj		İ
		expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize		
		or planarizing)) and (((crystalline or		
		crystal) near3 (silicon or si)) or		
		polysilicon)) and @ay<=2001) and		
		(lithography or lithographic or		
		photo\$1lithograph\$2)) and (((silicon adj		
		oxide) or (silicon adj dioxide) or siO or		
		SiO?sub.2) with (thermal or anneal or		
1_	2725	annealling)))) and (molybdenum or Mo) (ULE or (thermal adj expansion) or CTE!	He perm	2004/00/11
	2/23	or zerodur) and (polish or polishing or	US-PGPUB; EPO; JPO	2004/08/11
		cmp or planarize or planarizing)	Bro, UPO	12:03
-	1107	((ULE or (thermal adj expansion) or CTE!	US-PGPUB;	2004/08/11
		or zerodur) and (polish or polishing or	EPO; JPO	12:03
		cmp or planarize or planarizing)) and		
		@ay<=2001		
_	484	(((ULE or (thermal adj expansion) or CTE!	US-PGPUB;	2004/08/11
		or zerodur) and (polish or polishing or	EPO; JPO	12:04
		<pre>cmp or planarize or planarizing)) and @ay<=2001) and ((silicon adj oxide) or</pre>		
		(silicon adj dioxide) or siO or		
İ		SiO?sub.2)		
-	164	((((ULE or (thermal adj expansion) or	US-PGPUB;	2004/08/11
		CTE! or zerodur) and (polish or polishing	EPO; JPO	14:05
		or cmp or planarize or planarizing)) and		
		@ay<=2001) and ((silicon adj oxide) or		
		(silicon adj dioxide) or siO or		
		SiO?sub.2)) and (((crystalline or		
	ĺ	crystal) near3 (silicon or si)) or polysilicon)		
<u> </u>	L	POTABLITCOII)		

	r			
-	5	(USPAT	2004/08/11
}		("6048652") or ("6159643") or		15:00
		("6159824")).PN.		
_	1	("6613862").PN.	USPAT	2004/08/11
				15:00
-	1	("6613682").PN.	USPAT	2004/08/11
				15:34
-	12		USPAT	2004/08/11
		"5436205" "5492597" "5565681"		15:01
		"5605601" "5668038" "5753533"		
	·	"5759920" "5779926" "5866483").PN.		
_	711	mask near blank	USPAT	2004/08/11
				15:34
ļ -	11	(mask near blank) and ULE	USPAT	2004/08/11
				15:36
-	117	(mask near blank) and (polish or	USPAT	2004/08/11
		polishing or cmp or planarize or		15:46
		planarization or planarizing)		
-	112	((mask near blank) and (polish or	USPAT	2004/08/11
		polishing or cmp or planarize or		15:37
		planarization or planarizing)) not ((mask		
		near blank) and ULE)		
_	102	(POTEDII OF	USPAT	2004/08/11
		polishing or cmp or planarize or]	15:37
		planarization or planarizing)) not ((mask	-	
		near blank) and ULE)) and @ay<=2001		
_	23	(Politon of Politoning of CMD OI	USPAT	2004/08/11
		planarize or planarization or		16:16
		planarizing) and (ULE or (ultra adj low		
	5	adj expansion)) ("5272744" "5978441" "6048652"		
]	"6159643" "6159824").PN.	USPAT	2004/08/11
	11	ULE with (polish or polishing or cmp or	Hanam	15:50
	11	polished or planarize or planarizing)	USPAT	2004/08/11
	6	(ULE same (polish or polishing or cmp or	USPAT	16:19
		polished or planarize or planarizing))	USPAT	2004/08/11
		not (ULE with (polish or polishing or cmp		10:19
		or polished or planarize or planarizing))		1
-	17	ULE same (polish or polishing or cmp or	USPAT	2004/08/11
		polished or planarize or planarizing)	OPENI	16:20
		- Promoting)		1 10.20